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Patent

Customer No. 31561
Docket No. 13875-US-PA
Application No.: 10/710,199

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of
Applicant : Yang et al.
Application No. : 10/710,199
Filed : 2004/06/25
For : MOS TRANSISTOR AND FABRICATION THEREOF
Examiner : N/A
Art Unit : 2812

INFORMATION DISCLOSURE STATEMENT

ASSISTANT COMISSIONER FOR PATENTS
Arlington, VA22202

Enclosed is a PTO Form 1449 listing 5 reference(s), copy of which is attached. Applicant submits the reference(s) in compliance with his duty of disclosure pursuant to 37 CFR § 1.56 and 1.97. The Examiner is requested to make the citation(s) of official record.

This IDS is being submitted before the first Office Action. Thus, it is believed no fee is due.

The submission of the reference(s) should not be interpreted as admitting them as prior art.

Respectfully Submitted,
JIANQ CHYUN Intellectual Property Office

Date: August 19 2004

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FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE **INFORMATION DISCLOSURE STATEMENT BY APPLICATION**	ATTY. DOCKET NO.:13875-US-PA	APPLICATION NO.: 10/710,199
	APPLICANT: Yang et al.	
	FILING DATE: June 25, 2004	GROUP 2812

U.S. PATENT DOUCMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FIILNG DATE (IF APPROPRIATE)

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	FIILNG DATE (IF APPROPRIATE)

EXAMINER INITIAL		**OTHER DOCUMENTS** (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)
		Michaelson, " The work function of the elements and its periodicity", *JOURNAL OF APPLIED PHYSICS*, Vol. 48, No. 11, November 1977, pp.4729-4733.
		Zlatanovic et al., " Variation of reflectivity spectra, preferred orientation and stoichiometry of polycrystalline TiN films due to nitrogen flow variation" *PROC. 22nd INTERNATIONAL CONFERENCE ON MICROELECTRONICS (MIEL 2000)*, Vol. 1, NIS, SERBIA, 14-17, May 2000, pp. 261-264.
		Farahani et al. , " Limitation of the Tin/ Ti layer formed by the rapid thermal heat treatment of pure Ti films in an NH_3 ambient in fabrication of submicrometer CMOS flash EPROM IC's" , *IEEE TRANSACTIONS ON SEMICONDUCTOR MANUFACTURING*, Vol. 10, No. 1, February 1997, pp.147-153.
		Abe et al. " Cu damascene interconnects with crystallographic texture control and its electromigration performance", *IEEE 98CH36173. 36th ANNUAL INTERNATIONAL RELIABILITY PHYSICS SYMPOSIUMS*, RENO, NEVADA, 1998, pp.342-347.
		Sun et al. " A comparative study of CVD TiN and CVD TaN diffusion barriers for copper interconnection", 1995, pp. 18. 5.1-18. 5. 4.

EXAMINER	DATE CONSIDERED

EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED. INCLUDE COPY OF THIS FORM WITH NEST COMMUNICATION TO APPLICANT.